

## Low drop power Schottky rectifier

### Main product characteristics

$I_{F(AV)}$	2 x 10 A
$V_{RRM}$	40 V
$T_j$ (max)	150° C
$V_F$ (max)	0.5 V

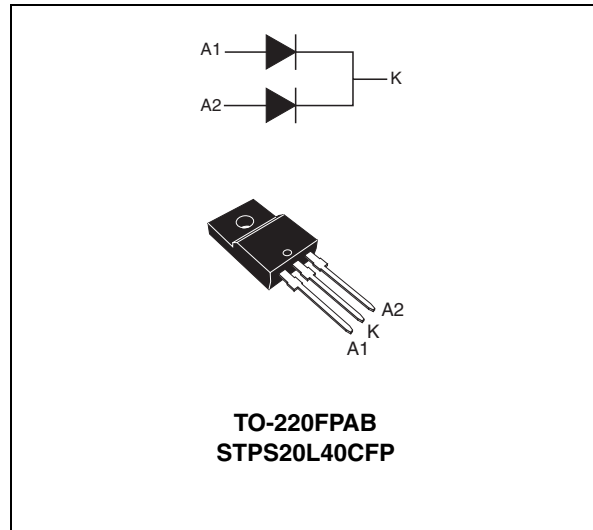
### Features and benefits

- Low forward voltage drop meaning very small conduction losses
- Low dynamic losses as a result of the schottky barrier
- Insulated package: TO-220FPAB  
insulating voltage = 200 V DC  
capacitance = 12 pF
- Avalanche capability specified

### Description

Dual center tap Schottky rectifiers designed for high frequency switched mode power supplies and DC to DC converters.

These devices are intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.



# 1 Characteristics

**Table 1. Absolute Ratings (limiting values)**

Symbol	Parameter		Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage		40	V
I <sub>F(RMS)</sub>	RMS forward voltage		30	A
I <sub>F(AV)</sub>	Average forward current	T <sub>c</sub> = 115° C δ = 0.5	Per diode 20 Per device	A
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms Sinusoidal	180	A
I <sub>RRM</sub>	Peak repetitive reverse current	t <sub>p</sub> = 2 μs square F = 1 kHz	1	A
I <sub>RSM</sub>	Non repetitive peak reverse current	t <sub>p</sub> = 100 μs square	2	A
P <sub>ARM</sub>	Repetitive peak avalanche power	t <sub>p</sub> = 1 μs T <sub>j</sub> = 25°C	4000	W
T <sub>stg</sub>	Storage temperature range		-65 to + 150	°C
T <sub>j</sub>	Maximum operating junction temperature <sup>(1)</sup>		150	°C
dV/dt	Critical rate of rise of reverse voltage		10000	V/μs

1.  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  condition to avoid thermal runaway for a diode on its own heatsink

**Table 2. Thermal resistances**

Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub>	Junction to case	Per diode Total Coupling	4.5 3.5 2.5	°C/W

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

**Table 3. Static electrical characteristics (per diode)**

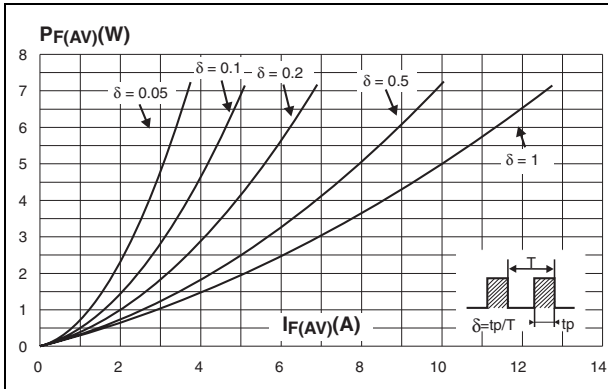
Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25° C	V <sub>R</sub> = V <sub>RRM</sub>			0.7	mA
		T <sub>j</sub> = 100° C			15	35	mA
V <sub>F</sub> <sup>(1)</sup>	Forward voltage drop	T <sub>j</sub> = 25° C	I <sub>F</sub> = 10 A			0.55	V
		T <sub>j</sub> = 125° C	I <sub>F</sub> = 10 A		0.44	0.5	
		T <sub>j</sub> = 25° C	I <sub>F</sub> = 20 A			0.73	
		T <sub>j</sub> = 125° C	I <sub>F</sub> = 20 A		0.62	0.72	

1. Pulse test: t<sub>p</sub> = 380 μs, δ < 2%

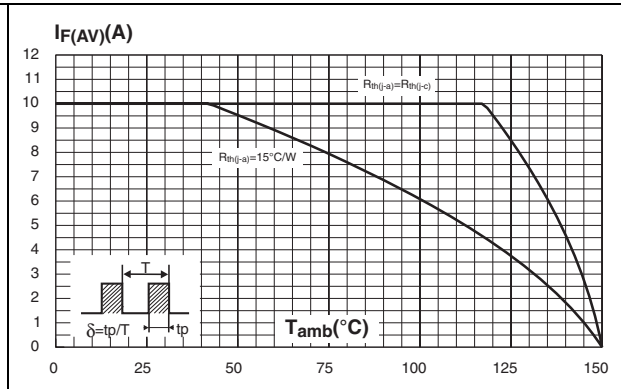
To evaluate the conduction losses use the following equation:

$$P = 0.28 \times I_{F(AV)} + 0.022 I_{F(RMS)}^2$$

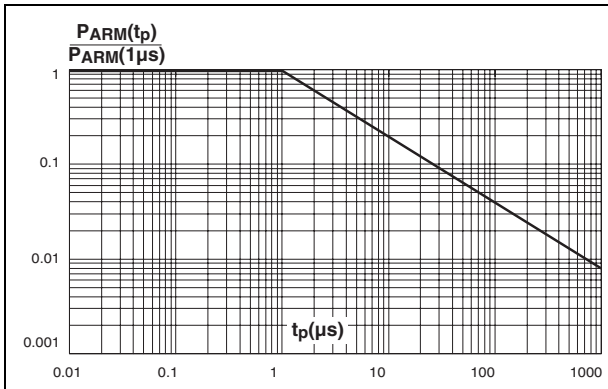
**Figure 1. Average forward power dissipation versus average forward current (per diode)**



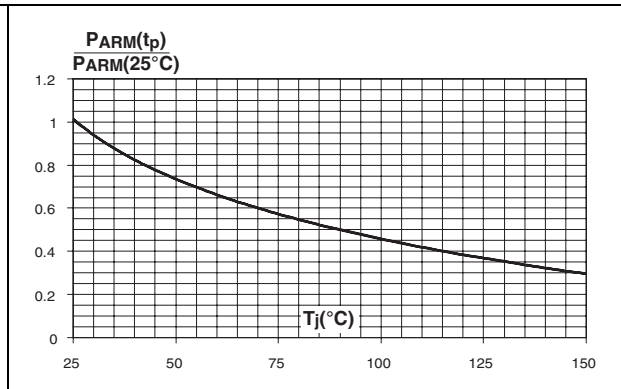
**Figure 2. Average forward current versus ambient temperature (delta = 0.5, per diode)**



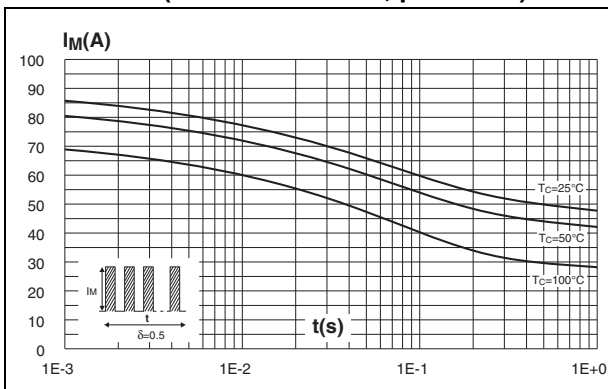
**Figure 3. Normalized avalanche power derating versus pulse duration**



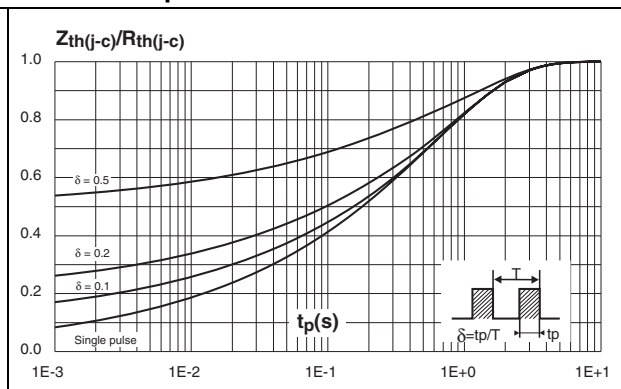
**Figure 4. Normalized avalanche power derating versus junction temperature**



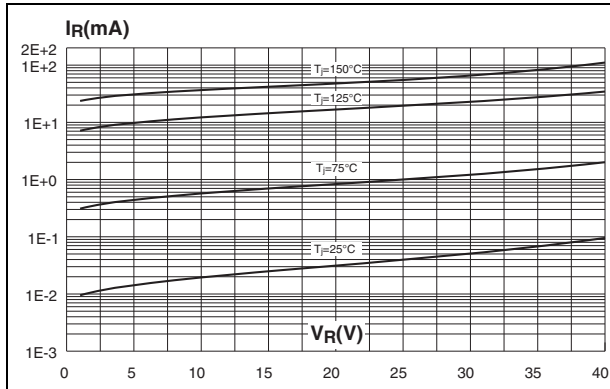
**Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)**



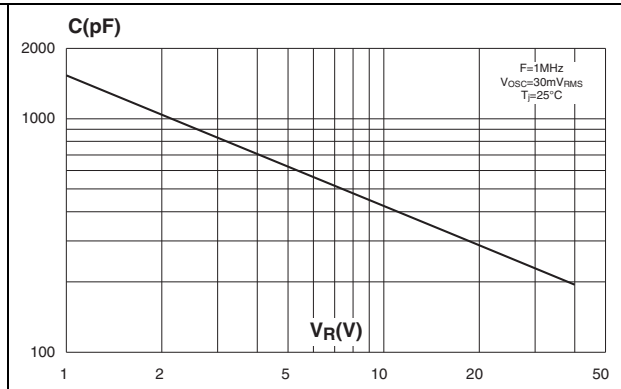
**Figure 6. Relative variation of thermal impedance junction to case versus pulse duration**



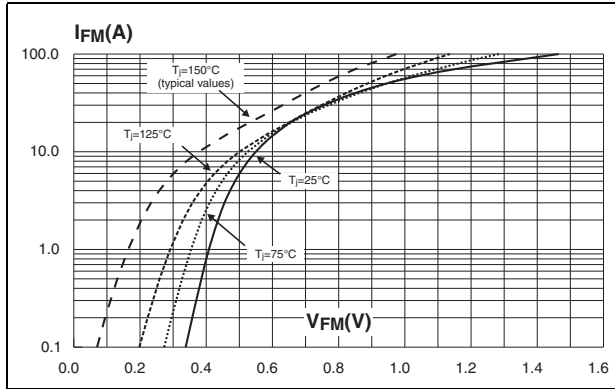
**Figure 7. Reverse leakage current versus reverse voltage applied (typical values, per diode)**



**Figure 8. Junction capacitance versus reverse voltage applied (typical values, per diode)**



**Figure 9. Forward voltage drop versus forward current (maximum values) (per diode)**



## 2 Package Information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 Nm
- Maximum torque value: 0.70 Nm

**Table 4. TO-220FPAB dimensions**

Ref	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	2.5	2.7	0.098	0.106
D	2.5	2.75	0.098	0.108
E	0.45	0.70	0.018	0.027
F	0.75	1	0.030	0.039
F1	1.15	1.70	0.045	0.067
F2	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.4	2.7	0.094	0.106
H	10	10.4	0.393	0.409
L2	16 Typ.		0.63 Typ.	
L3	28.6	30.6	1.126	1.205
L4	9.8	10.6	0.386	0.417
L5	2.9	3.6	0.114	0.142
L6	15.9	16.4	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia.	3.00	3.20	0.118	0.126

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com).

### 3 Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS20L40CFP	STPS20L40CFP	TO-220FPAB	2 g	50	Tube

### 4 Revision history

Date	Revision	Description of Changes
Jul_2003	4B	Last release.
26-Mar-2007	5	Removed ISOWATT, TO-220AB and TO-247 packages.

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